

L Number	Hits	Search Text	DB	Time stamp
3	69	electromagnet\$3 same (Gan or (p-type adj Gan) or (III-V adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 09:19
-	60	semiconductor and "hole density" and nitride and (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:36
-	29	"hole density" and nitride and (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4)) and "p-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:39
-	182	("hole density" or "carrier density") and nitride and (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4)) and "p-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:42
-	48	("hole density" or "carrier density") and nitride and (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4)) and "p-type" and "III-V"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:47
-	186	((("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4))) and "p-type" and "III-V" and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:51
-	119	((("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4))) and "p-type" and "III-V" and nitride and hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 11:53
-	103	((("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or (rapid adj thermal) or (heat adj treat\$4))) and "p-type" and "III-V" and nitride and hydrogen and grow\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 14:35
-	101	((("hole density" or "carrier density" or (resistance or resistivity))) same ((anneal or annealed or annealing) or PTP or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or treatment))) and "p-type" and "III-V" and nitride and hydrogen and grow\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 14:47
-	109	((("hole density" or "carrier density" or (resistance or resistivity))) same ((anneal or annealed or annealing) or PTP or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or treatment))) and "p-type" and "III-V" and nitride and hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 14:52
-	136	((("hole density" or "carrier density" or (resistance or resistivity))) same ((anneal or annealed or annealing) or PTP or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or treatment))) and (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:10
-	14	07/970,145	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 15:04
-	0	07/970,145.rlan.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 15:04

-	2	970,145.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 15:04
-	92	((("hole density" or "carrier density" or (resistance or resistivity))) same ((anneal or annealed or annealing) or PTP or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or treatment))) and (p-type adj GaN) and (etch or etching or etchant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/18 17:13
-	96	((("hole density" or "carrier density" or (resistance or resistivity)) same (etch or etching or etchant or plasma)) and (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:22
-	34	((("hole density" or "carrier density" or (resistance or resistivity)) same (etch or etching or etchant or plasma)) same (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:19
-	181	(etch or etching or etchant or plasma) same (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:28
-	96	((("hole density" or "carrier density" or (resistance or resistivity)) same (etch or etching or etchant or plasma)) and (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:20
-	100	((("hole density" or "carrier density" or (resistance or resistivity)) same (clean or cleaned or cleaning or koh or naoh or nh4oh etch or etching or etchant or plasma)) and (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:26
-	22	(koh or naoh or nh4oh) and (p-type adj GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:31
-	314	(koh or naoh or nh4oh) and GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 09:31
-	31	(koh or naoh or nh4oh) same GaN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:16
-	2159	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (etch or etching or etchant or Naoh or Koh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:10
-	146	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (etch or etching or etchant or Naoh or Koh) same (resistivity or resistance)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 11:04
-	9	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (etch or etching or etchant or Naoh or Koh) same (resistivity or resistance) same hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:34

-	412	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (passivation or passivating or passivate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:35
-	58	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (passivation or passivating or passivate) same (hydrogen or h or h2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:37
-	10	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (passivation or passivating or passivate) same (hydrogen or h or h2) same (Etch or etchant or etching)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:42
-	4	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same ((hydrogen or H) adj remov\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 10:43
-	87	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGaN or AlGaN) same (surface adj treat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 11:45
-	25	(GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGaN or AlGaN) same (surface adj treat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 11:47
-	32	(GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or AlInGaN or AlGaN) same (Naoh or Koh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:11
-	6756	(etch or etching or etchant or plasma) same resistivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:29
-	1016	(etch or etching or etchant or plasma) same resistivity same (GaN or (p-type adj GaN) or "III-V" or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:31
-	33	(etch or etching or etchant or plasma) same resistivity same ((p-type adj GaN) or GaN or "III-V")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:32
-	58	(clean or cleaning or removing or hydrogen) same resistivity same ((p-type adj GaN) or GaN or "III-V")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:36
-	9	(clean or cleaning or removing) same resistivity same ((p-type adj GaN) or GaN or "III-V")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:48
-	1	(chemical adj treatment) same resistivity same ((p-type adj GaN) or GaN or "III-V")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:48
-	3554	clean and (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:55

-	247	clean and (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or naoh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 13:58
-	20	clean same (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or naoh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 14:15
-	134	plasma same (GaN or p-GaN or "p-type GaN" or "III-V nitride" or p-type) and (koh or naoh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 17:27
-	3	022,364.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 14:22
-	3	020,629.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 14:23
-	0	"Etching adj GaN" and "DC adj plasma"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 14:24
-	641	ultrasonic\$3 and clean\$3 and (GaN or (p-type adj Gan) or p-type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:47
-	108	ultrasonic\$3 and clean\$3 same (GaN or (p-type adj Gan) or p-type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:47
-	32	ultrasonic\$3 same clean\$3 same (GaN or (p-type adj Gan) or p-type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:50
-	5	ultrasonic\$3 same clean\$3 same (GaN or (p-type adj Gan))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:51
-	16	ultrasonic\$3 same (GaN or (p-type adj Gan))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:52
-	563	ultrasonic\$3 same (GaN or (p-type adj Gan) or nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:52
-	16	ultrasonic\$3 same (GaN or (p-type adj Gan) or (III-V adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/22 09:18
-	30	ultrasonic\$3 same (GaN or (p-type adj Gan) or (III-V))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 16:53

-	18	plasma same (GaN or p-GaN or "p-type GaN" or "III-V nitride") and (koh or naoh or nh4oh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/19 17:28
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